

Electronic Supplementary Material (ESI) for RSC Advances

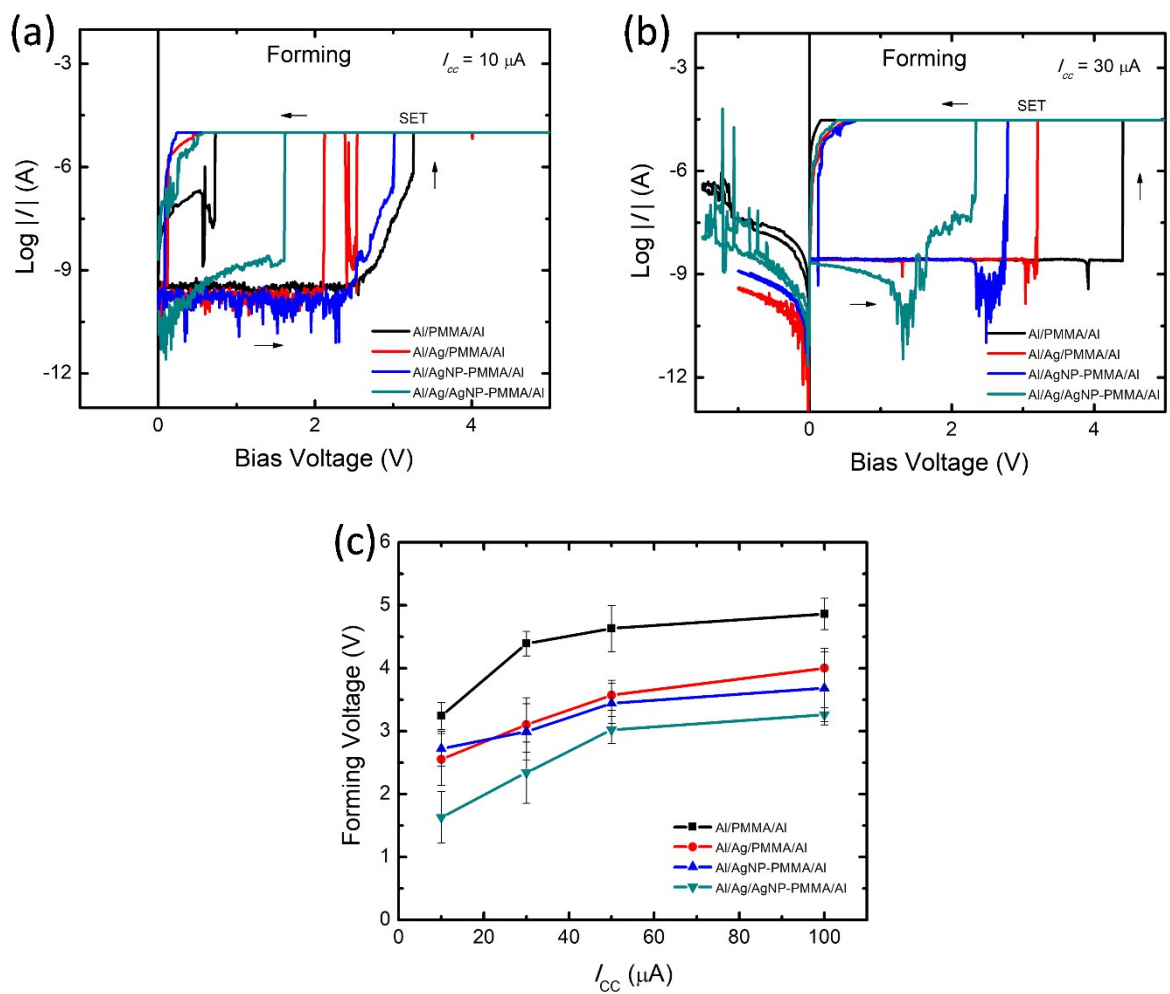
## **Configurable Switching Behavior in the Polymer-based Resistive Memories by Adopting Unique Electrode/Electrolyte Arrangement**

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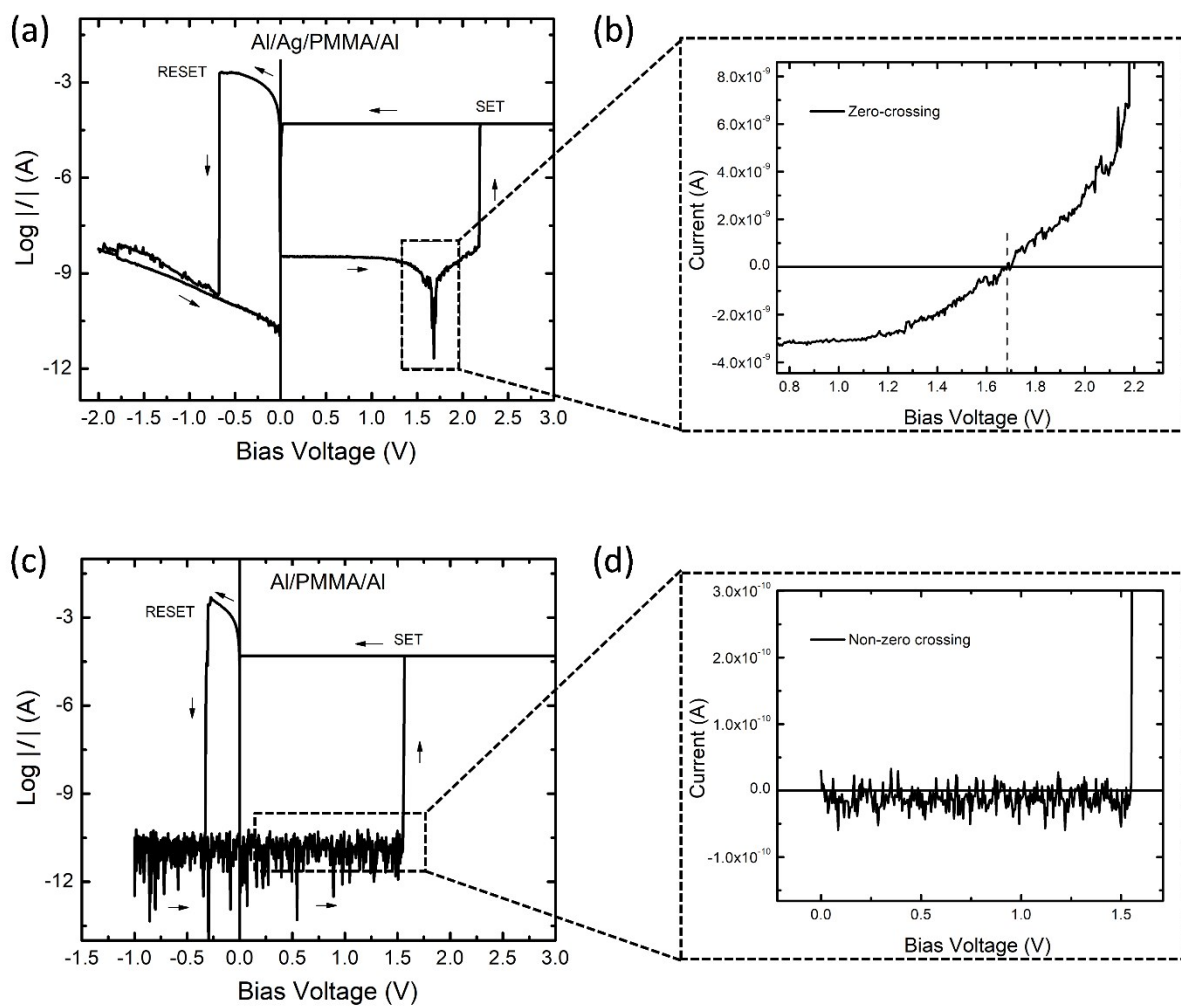
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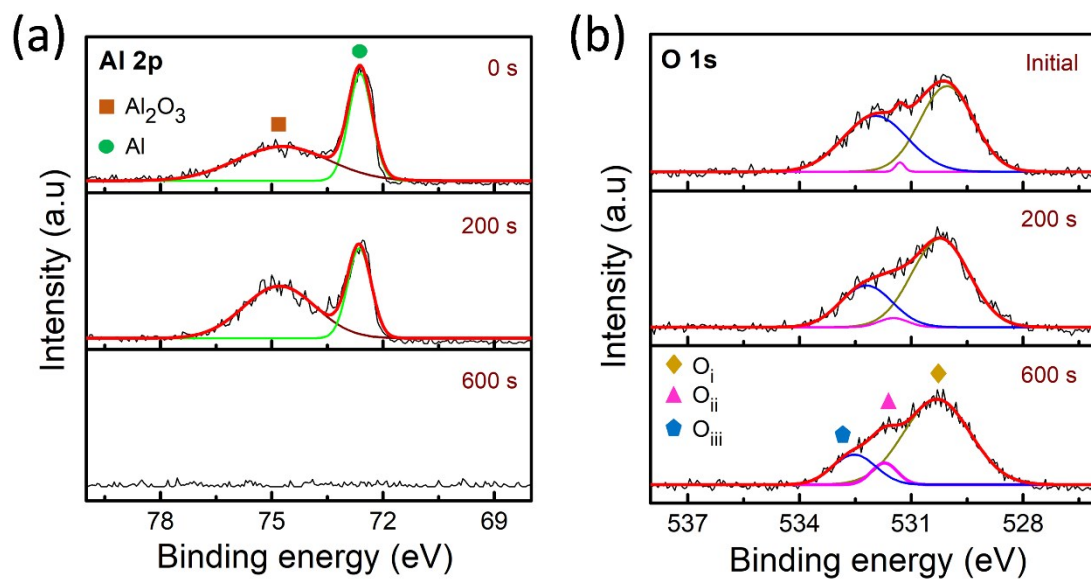
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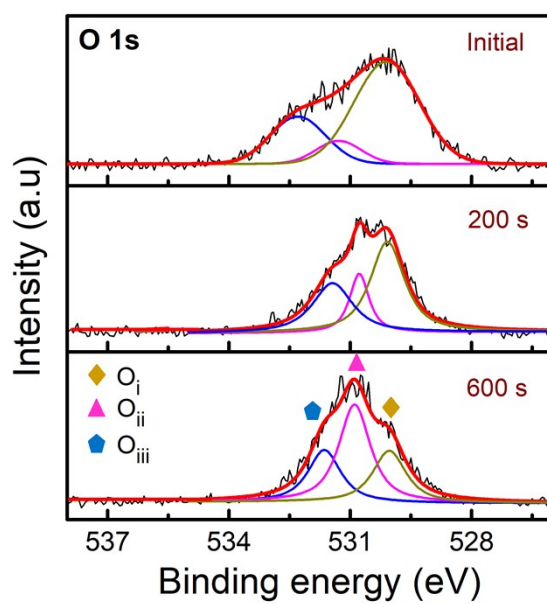
**Fig. S1** The  $I$ - $V$  plots of the forming process of the devices measured under (a)  $I_{CC} = 10 \mu\text{A}$ , (b)  $I_{CC} = 30 \mu\text{A}$  and (c) the plot between  $I_{CC}$  and forming voltage (evaluated from the  $I$ - $V$  data of 5 devices at each  $I_{CC}$ ).



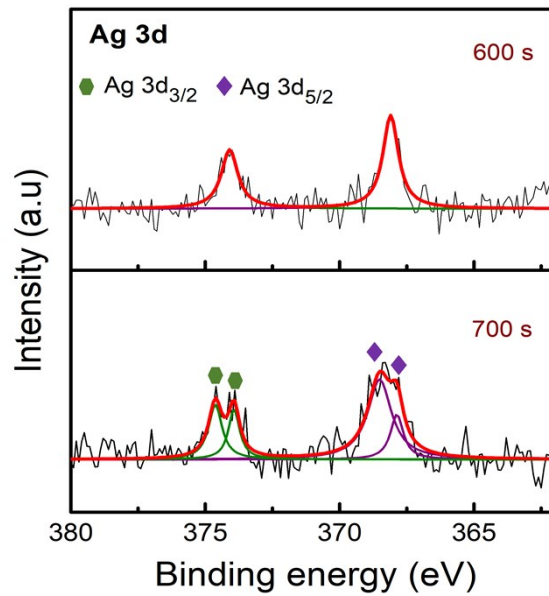
**Fig. S2** (a and c) The current minimum in a logarithmic scale of the  $I-V$  behaviour, corresponding to a (b) zero-current crossing point and (d) non-zero current crossing in a linear scale of the Al/Ag/PMMA/Al and Al/PMMA/Al devices, respectively.



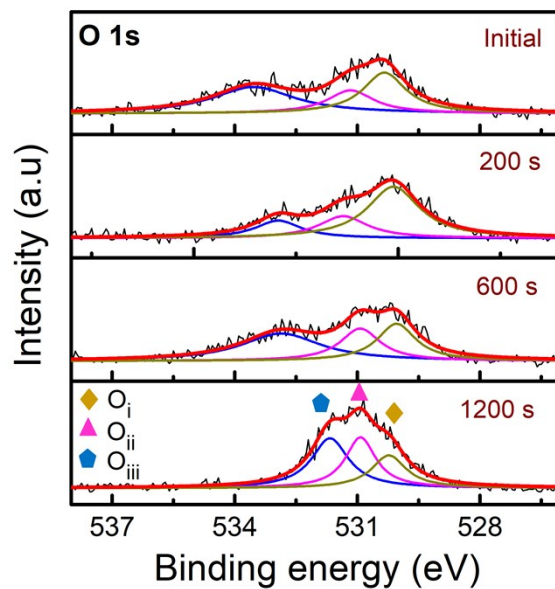
**Fig. S3** Depth-profiling XPS scans of (a) Al 2p and (b) O 1s signals of the pristine Al/PMMA/Al device (HRS).



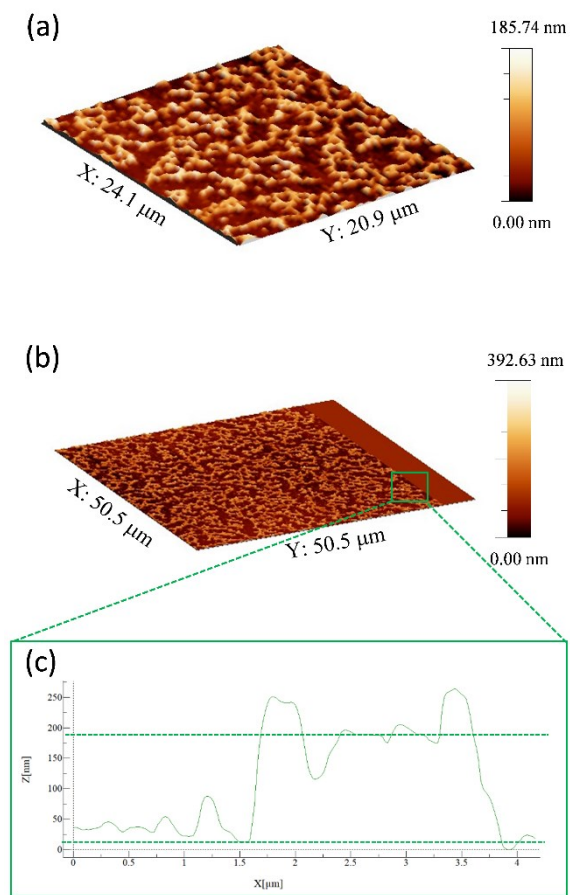
**Fig. S4** O 1s signals of the depth-profiling XPS spectra of Al/AgNP-PMMA/Al device.



**Fig. S5** Ag 3d signals of the depth-profiling XPS spectra of Al/AgNP-PMMA/Al device.



**Fig. S6** O 1s signals of the depth-profiling XPS spectra of Al/Ag/PMMA/Al device.



**Fig. S7** (a) AFM image of the pure PMMA film and (b) AFM image of the etched film and (c) the corresponding thickness variation profile. The thickness of film is  $\sim 200$  nm.

**Table S1.** The mean value ( $\mu$ ) and standard deviation ( $\sigma$ ) of the  $V_{\text{SET}}/V_{\text{RESET}}$  and  $R_{\text{LRS}}/R_{\text{HRS}}$  data of all the devices

Device	Mean value ( $\mu$ ) / Standard deviation ( $\sigma$ )		Mean value ( $\mu$ ) / Standard deviation ( $\sigma$ )	
	$V_{\text{SET}}$ (V)	$V_{\text{RESET}}$ (V)	$R_{\text{LRS}}$ ( $\Omega$ )	$R_{\text{HRS}}$ ( $\Omega$ )
Al/PMMA/Al	2.28/ 0.70	-0.48/ 0.29	165.7/ 211.6	$2.59 \times 10^9$ / $2.64 \times 10^9$
Al/Ag/PMMA/Al	2.30/ 0.74	-0.88/ 0.38	218.5/ 210.2	$4.58 \times 10^7$ / $4.94 \times 10^7$
Al/AgNP-PMMA/Al	2.37/ 0.63	-0.44/ 0.17	67.9/ 117.7	$6.50 \times 10^9$ / $1.16 \times 10^{10}$
Al/Ag/AgNP-PMMA/Al	1.73/ 0.61	-0.36/ 0.17	419.8/ 312.1	$4.65 \times 10^7$ / $4.23 \times 10^7$